



SOD-323 Plastic-Encapsulate Diodes

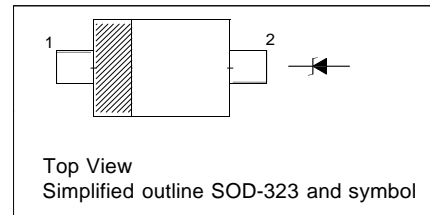
BZT52C2V4S-BZT52C75S ZENER DIODE

FEATURES

- Planar die construction
- 200mW power dissipation on ceramic PBC
- General purpose, medium current
- Ideally suited for automated assembly processes
- Available in lead free version

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Maximum Ratings ($T_a=25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Value	Unit
Forward Voltage (Note 2) @ $I_F = 10\text{mA}$	V_F	0.9	V
Power Dissipation(Note 1)	P_D	200	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~+150	$^\circ\text{C}$



Electrical Characteristics($T_a = 25^\circ\text{C}$ unless otherwise specified)

TYPE	Marking	Zener Voltage Range (Note 2)				Maximum Zener Impedance (Note 3)			Maximum Reverse Current (Note 2)		Typical Temperature Coefficient @ I_{ZTC} mV/ $^\circ\text{C}$		Test Current I_{ZTC}
		$V_Z@I_{ZT}$			I_{ZT}	$Z_{ZT}@I_{ZT}$	$Z_{ZK}@I_{ZK}$	I_{ZK}	I_R	V_R	Min	Max	
		Nom(V)	Min(V)	Max(V)	(mA)	Ω	(mA)	μA	V	mA			
BZT52C2V4S	W0	2.4	2.20	2.60	5	100	600	1.0	50	1.0	-3.5	0	5
BZT52C2V7S	W1	2.7	2.5	2.9	5	100	600	1.0	20	1.0	-3.5	0	5
BZT52C3V0S	W2	3.0	2.8	3.2	5	95	600	1.0	10	1.0	-3.5	0	5
BZT52C3V3S	W3	3.3	3.1	3.5	5	95	600	1.0	5	1.0	-3.5	0	5
BZT52C3V6S	W4	3.6	3.4	3.8	5	90	600	1.0	5	1.0	-3.5	0	5
BZT52C3V9S	W5	3.9	3.7	4.1	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V3S	W6	4.3	4.0	4.6	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V7S	W7	4.7	4.4	5.0	5	80	500	1.0	3	2.0	-3.5	0.2	5
BZT52C5V1S	W8	5.1	4.8	5.4	5	60	480	1.0	2	2.0	-2.7	1.2	5
BZT52C5V6S	W9	5.6	5.2	6.0	5	40	400	1.0	1	2.0	-2	2.5	5
BZT52C6V2S	WA	6.2	5.8	6.6	5	10	150	1.0	3	4.0	0.4	3.7	5
BZT52C6V8S	WB	6.8	6.4	7.2	5	15	80	1.0	2	4.0	1.2	4.5	5
BZT52C7V5S	WC	7.5	7.0	7.9	5	15	80	1.0	1	5.0	2.5	5.3	5
BZT52C8V2S	WD	8.2	7.7	8.7	5	15	80	1.0	0.7	5.0	3.2	6.2	5
BZT52C9V1S	WE	9.1	8.5	9.6	5	15	100	1.0	0.5	6.0	3.8	7.0	5
BZT52C10S	WF	10	9.4	10.6	5	20	150	1.0	0.2	7.0	4.5	8.0	5
BZT52C11S	WG	11	10.4	11.6	5	20	150	1.0	0.1	8.0	5.4	9.0	5
BZT52C12S	WH	12	11.4	12.7	5	25	150	1.0	0.1	8.0	6.0	10.0	5
BZT52C13S	WI	13	12.4	14.1	5	30	170	1.0	0.1	8.0	7.0	11.0	5
BZT52C15S	WJ	15	13.8	15.6	5	30	200	1.0	0.1	10.5	9.2	13	5
BZT52C16S	WK	16	15.3	17.1	5	40	200	1.0	0.1	11.2	10.4	14	5
BZT52C18S	WL	18	16.8	19.1	5	45	225	1.0	0.1	12.6	12.4	16	5
BZT52C20S	WM	20	18.8	21.2	5	55	225	1.0	0.1	14.0	14.4	18.0	5
BZT52C22S	WN	22	20.8	23.3	5	55	250	1.0	0.1	15.4	16.4	20.0	5
BZT52C24S	WO	24	22.8	25.6	5	70	250	1.0	0.1	16.8	18.4	22.0	5
BZT52C27S	WP	27	25.1	28.9	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52C30S	WQ	30	28.0	32.0	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52C33S	WR	33	31.0	35.0	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52C36S	WS	36	34.0	38.0	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52C39S	WT	39	37.0	41.0	2	130	350	0.5	0.1	27.3	33.4	41.2	2
BZT52C43S	WU	43	40.0	46.0	2.5	130	500	1.0	2.0	33.0	10.0	12.0	2.5
BZT52C47S	WV	47	44.0	50.0	2.5	150	500	1.0	2.0	36.0	10.0	12.0	2.5
BZT52C51S	WW	51	48.0	54.0	2.5	180	500	1.0	1.0	39.0	10.0	12.0	2.5
BZT52C56S	WX	56	52.0	60.0	2.5	180	500	1.0	1.0	43.0	10.0	12.0	2.5
BZT52C62S	WY	62	58.0	66.0	2.5	200	500	1.0	0.2	47.0	10.0	12.0	2.5
BZT52C68S	WZ	68	64.0	72.0	2.5	250	500	1.0	0.2	52.0	10.0	12.0	2.5
BZT52C75S	ZA	75	70.0	79.0	2.5	300	500	1.0	0.2	57.0	10.0	12.0	2.5

- Notes: 1. Device mounted on ceramic PCB: 7.6mm x 9.4mm x 0.87mm with pad areas 25mm².
 2. Short duration test pulse used to minimize self-heating effect.
 3. f = 1kHz.



Typical Characteristics

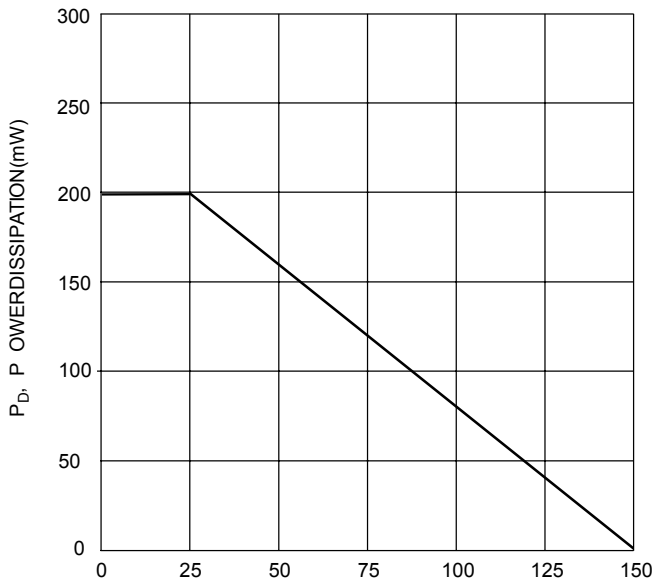


Fig. 1 Power Dissipation vs Ambient Temperature

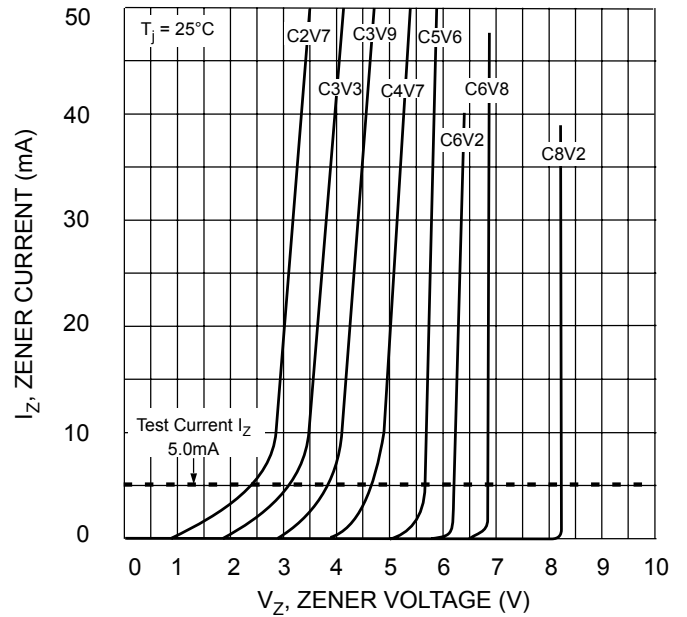


Fig. 2 Zener Breakdown Characteristics

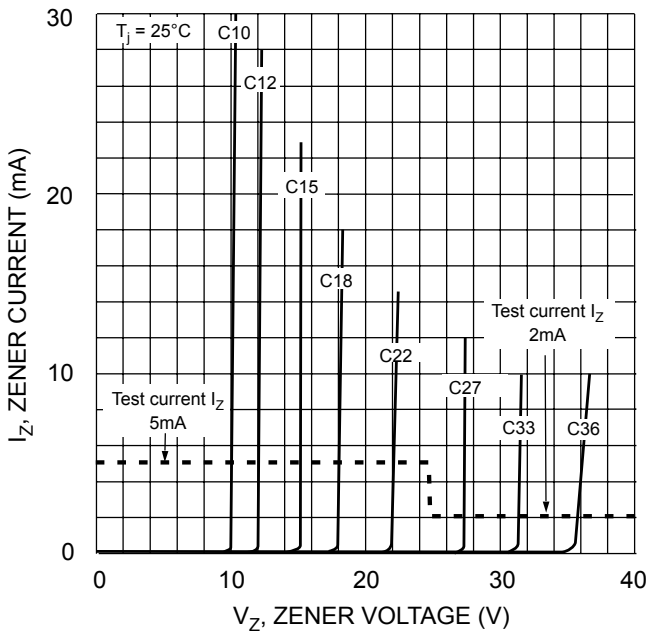


Fig. 3 Zener Breakdown Characteristics

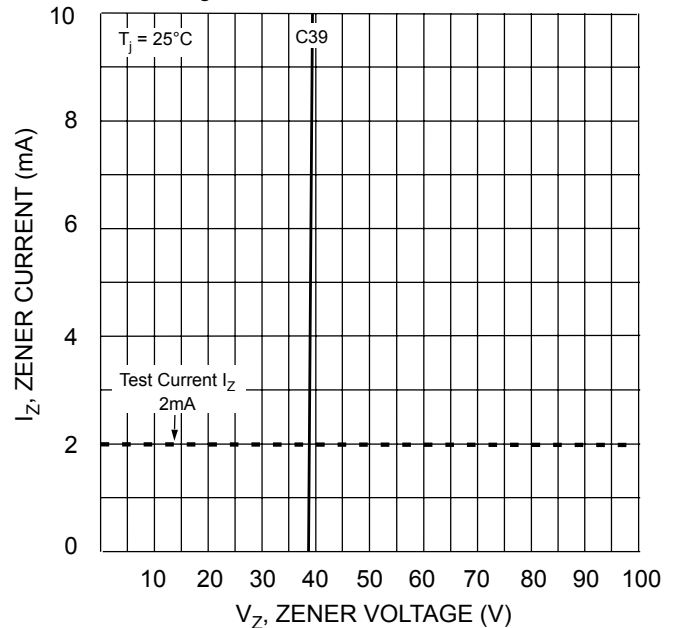


Fig. 4 Zener Breakdown Characteristics

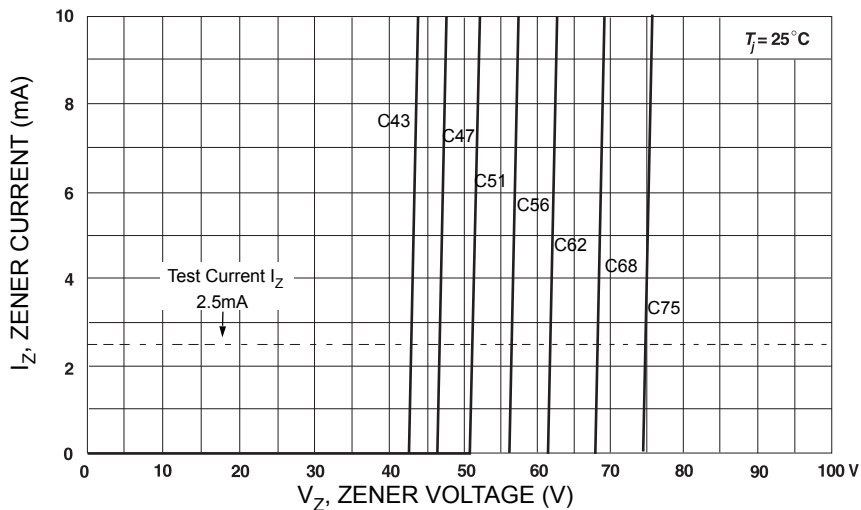
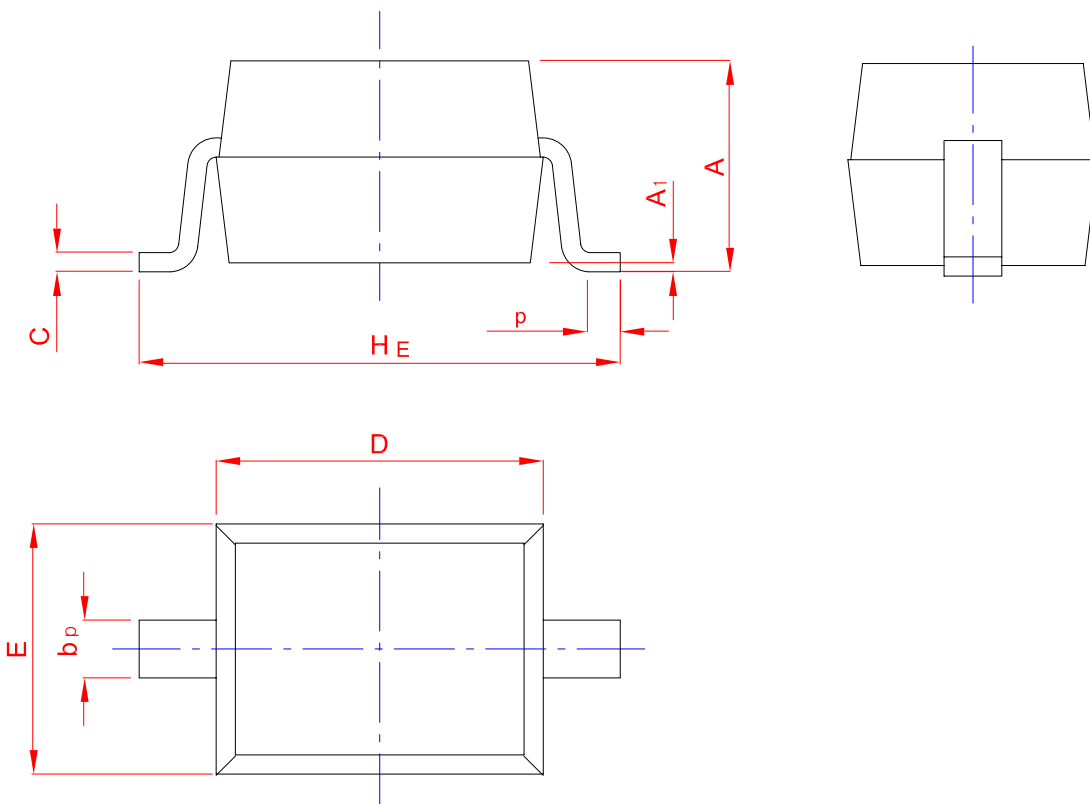
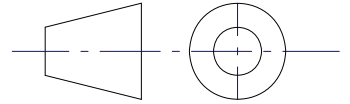


Fig. 5 Zener Breakdown Characteristics



Plastic surface mounted package; 2 leads

PACKAGE OUTLINE SOD-323



UNIT	A	b _p	C	D	E	H _E	A ₁	L _p
mm	1.20	0.40	0.15	1.80	1.35	2.80	0.10	0.50
	0.90	0.25	0.10	1.60	1.15	2.30	0.01	0.20